



查询42672-99供应商

# Peregrine Semiconductor

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## Advance Information PE42672 DIE

### SP7T UltraCMOS™ 2.75 V Switch 100 – 3000 MHz, +68 dBm IIP3

Figure 1. Functional Diagram

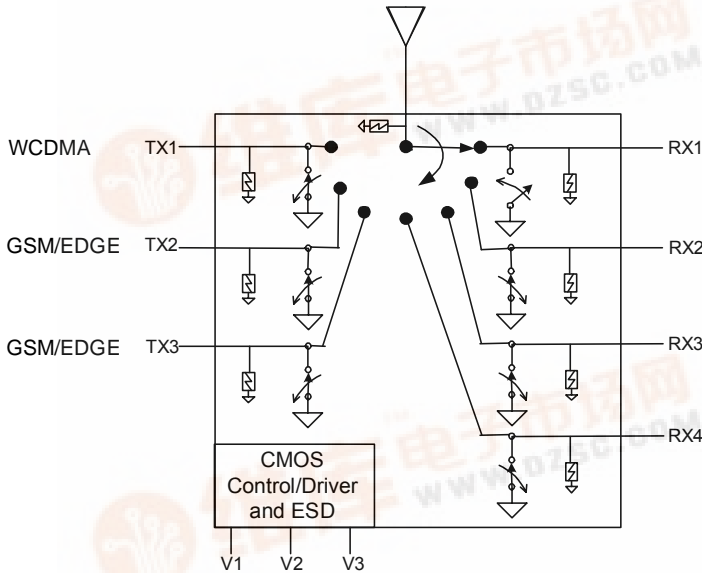
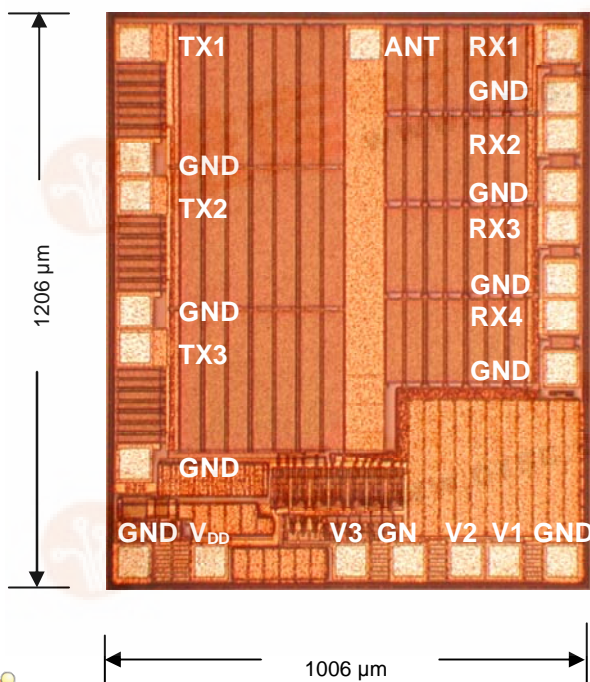


Figure 2. Die Top View\*



### Features

- Dedicated TX1 port for WCDMA, TX2 and TX3 ports for GSM/EDGE
- Three pin CMOS logic control with integral decoder/driver
- Exceptional harmonic performance:  $2f_o = -84$  dBc and  $3f_o = -77$  dBc
- Low TX insertion loss: 0.50 dB at 900 MHz, 0.70 dB at 1900 MHz
- TX – RX Isolation of 44 dB at 900 MHz, 38 dB at 1900 MHz
- 1500 V HBM ESD tolerance all ports
- +68 dBm IIP3
- -111 dBm IMD3
- No blocking capacitors required

### Product Description

The PE42672 is a HaRP™-enhanced SP7T RF Switch developed on the UltraCMOS™ process technology. It addresses the specific design needs of the Quad-Band GSM Handset Antenna Switch Module Market for use in GSM/EDGE/PCS/DCS/WCDMA handsets. The switch is comprised of three TX ports and four RX ports. TX1 is designed for WCDMA and TX2 and TX3 are designed for GSM/EDGE. The four symmetric RX ports can be used for GSM/EDGE/PCS RX. On-chip CMOS decoder logic facilitates three-pin low voltage CMOS control, while high ESD tolerance of 1500 V at all ports, no blocking capacitor requirements, and on-chip SAW filter over-voltage protection devices make this the ultimate in integration and ruggedness.

Peregrine's HaRP™ technology enhancements deliver high linearity and exceptional harmonics performance. It is an innovative feature of the UltraCMOS™ process, providing performance superior to GaAs with the economy and integration of conventional CMOS.



**Table 1. Target Electrical Specifications @ 25 °C, V<sub>DD</sub> = 2.75 V**

Parameter	Condition	Typ	Units
Insertion loss <sup>1</sup>	TX - Ant (850 / 900)	0.5	dB
	TX - Ant (1800 / 1900)	0.7	dB
	TX - Ant ( 2200 UMTS )	0.8	dB
	RX - Ant (850 / 900)	0.8	dB
	RX - Ant (1800 / 1900)	1.0	dB
Return Loss	Port under test in on state	20	dB
Isolation	TX - RX (850 / 900)	44	dB
	TX - RX (1800 / 1900)	38	dB
	TX - TX (850 / 900)	29	dB
	TX - TX (1800 / 1900)	23	dB
	TX1 - RX (1900 / 2200)	37	dB
2nd Harmonic	TX 850 / 900 MHz, +35 dBm output power, 50 Ω	-84	dBc
	TX 1800 / 1900 MHz, +33 dBm output power, 50 Ω	-80	dBc
3rd Harmonic	TX 850 / 900 MHz, +35 dBm output power, 50 Ω	-77	dBc
	TX 1800 / 1900 MHz, +33 dBm output power, 50 Ω	-73	dBc
IMD3 distortion at 2.14 GHz	TX1 Measured at 2.14 GHz at Ant port, input +20 dBm CW signal at 1.95 GHz and -15 dBm CW signal at 1.76 GHz	-111	dBm

Note: 1. Insertion loss specified with optimal impedance matching.

**Table 2. Operating Ranges**

Parameter	Symbol	Min	Typ	Max	Units
Temperature range	T <sub>OP</sub>	-40		+85	°C
V <sub>DD</sub> Supply Voltage	V <sub>DD</sub>	2.65	2.75	2.85	V
I <sub>DD</sub> Power Supply Current (V <sub>DD</sub> = 2.75 V)	I <sub>DD</sub>		13	50	μA
TX input power <sup>2</sup> (VSWR ≤ 3:1)	P <sub>IN</sub>			+35	dBm
RX input power <sup>2</sup> (VSWR =1:1)	P <sub>IN</sub>			+20	dBm
Control Voltage High	V <sub>IH</sub>	1.4			V
Control Voltage Low	V <sub>IL</sub>			0.4	V

Note: 2. Assumes RF input period of 4620 μs and duty cycle of 50%.

**Table 3. Absolute Maximum Ratings**

Symbol	Parameter/Conditions	Min	Max	Units
V <sub>DD</sub>	Power supply voltage	-0.3	4.0	V
V <sub>I</sub>	Voltage on any input	-0.3	V <sub>DD</sub> + 0.3	V
T <sub>ST</sub>	Storage temperature range	-65	+150	°C
P <sub>IN</sub> (50 Ω)	TX input power (50 Ω) <sup>3,4</sup>		+38	dBm
	RX input power (50 Ω) <sup>3,4</sup>		+23	
P <sub>IN</sub> (∞:1)	TX input power (VSWR = ∞:1) <sup>3,4</sup>		+35	dBm
V <sub>ESD</sub>	ESD Voltage (HBM, MIL_STD 883 Method 3015.7)		1500	V
	ESD Voltage at ANT Port (IEC 61000-4-2)		1700	V

Note: 3. Assumes RF input period of 4620 μs and duty cycle of 50%.

4. V<sub>DD</sub> within operating range specified in Table 2.

Part performance is not guaranteed under these conditions. Exposure to absolute maximum conditions for extended periods of time may adversely affect reliability. Stresses in excess of absolute maximum ratings may cause permanent damage.

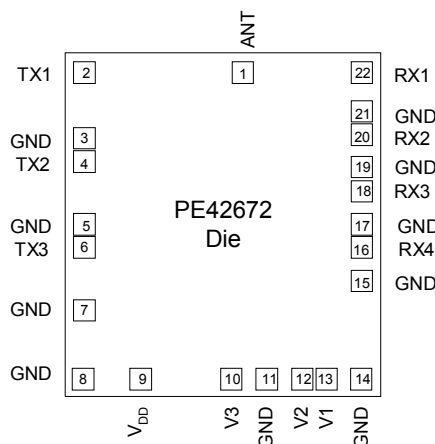
**Table 4. Pin Descriptions**

Pin No.	Pin Name	Description
1	ANT	RF Common – Antenna
2 <sup>6</sup>	TX1	RF I/O - TX1
3 <sup>5</sup>	GND	Ground (Requires two bond wires)
4 <sup>6</sup>	TX2	RF I/O – TX2
5 <sup>5</sup>	GND	Ground
6 <sup>5</sup>	TX3	RF I/O – TX3
7 <sup>5</sup>	GND	Ground
8 <sup>5</sup>	GND	Ground
9	V <sub>DD</sub>	Supply
10	V3	Switch control input, CMOS logic level
11 <sup>5</sup>	GND	Ground
12	V2	Switch control input, CMOS logic level
13	V1	Switch control input, CMOS logic level
14 <sup>5</sup>	GND	Ground
15 <sup>5</sup>	GND	Ground
16 <sup>6</sup>	RX4	RF I/O – RX4
17 <sup>5</sup>	GND	Ground
18 <sup>6</sup>	RX3	RF I/O – RX3
19 <sup>5</sup>	GND	Ground
20 <sup>6</sup>	RX2	RF I/O – RX2
21 <sup>5</sup>	GND	Ground
22 <sup>6</sup>	RX1	RF I/O – RX1

Notes: 5. Bond wires should be physically short and connected to ground plane for best performance.

6. Blocking capacitors needed only when non-zero DC voltage present.

**Figure 3. Pad Configuration (Top View)**



**Table 5. Truth Table**

Path	V1	V2	V3
RX1 - ANT	0	0	0
RX2 - ANT	1	0	0
RX3 - ANT	0	1	0
RX4 - ANT	1	1	0
TX1 - ANT	0	0	1
TX2 - ANT	1	0	1
TX3 - ANT	0	1	1
All Off	1	1	1

**Electrostatic Discharge (ESD) Precautions**

When handling this UltraCMOS™ device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the specified rating.

**Latch-Up Avoidance**

Unlike conventional CMOS devices, UltraCMOS™ devices are immune to latch-up.

**Table 6. Ordering Information**

Order Code	Description	Package	Shipping Method
42672-90	PE42672-DIE-D	Film Frame	Wafer (Gross Die / Wafer Quantity)
42672-99	PE42672-DIE-400G	Waffle Pack	400 Dice / Waffle Pack
42672-00	PE42672-DIE-1H	Evaluation Kit	1/ box

## Sales Offices

### *The Americas*

#### **Peregrine Semiconductor Corp.**

9450 Carroll Park Drive  
San Diego, CA 92121  
Tel 858-731-9400  
Fax 858-731-9499

### *Europe*

#### **Peregrine Semiconductor Europe**

##### **Commercial Products:**

Bâtiment Maine  
13-15 rue des Quatre Vents  
F- 92380 Garches, France  
Tel: +33-1-47-41-91-73  
Fax : +33-1-47-41-91-73

##### **Space and Defense Products:**

180 Rue Jean de Guiramand  
13852 Aix-En-Provence cedex 3, France  
Tel: +33(0) 4 4239 3361  
Fax: +33(0) 4 4239 7227

### *North Asia Pacific*

#### **Peregrine Semiconductor K.K.**

5A-5, 5F Imperial Tower  
1-1-1 Uchisaiwaicho, Chiyoda-ku  
Tokyo 100-0011 Japan  
Tel: +81-3-3502-5211  
Fax: +81-3-3502-5213

### *South Asia Pacific*

#### **Peregrine Semiconductor**

28G, Times Square,  
No. 500 Zhangyang Road,  
Shanghai, 200122, P.R. China  
Tel: +86-21-5836-8276  
Fax: +86-21-5836-7652

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The product is in a formative or design stage. The data sheet contains design target specifications for product development. Specifications and features may change in any manner without notice.

### **Preliminary Specification**

The data sheet contains preliminary data. Additional data may be added at a later date. Peregrine reserves the right to change specifications at any time without notice in order to supply the best possible product.

### **Product Specification**

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